650 nm LD Epiwafer

Descriptions

The 650nm LD epiwafer is comprised with InGaP/InAlGaP material multiple quantum-Well as the active layer. Both pointer and DVD laser epiwafers are available.

Wafer Characterization

The epiwafers are characterized by PL, DCXD and CV tests. ***Figure 1*** through ***Figure 3*** show the typical results of our epiwafer. The PL wavelength mapping for 1200 points in the inner 40 mm of a 2" wafer shows stand deviation of 0.6nm.

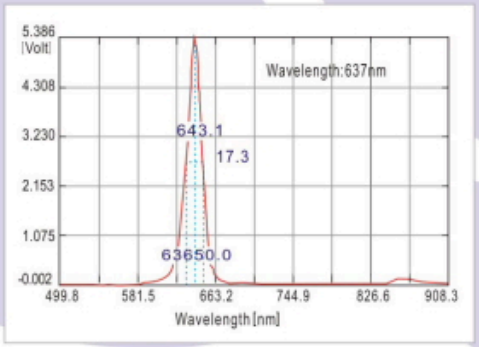

FIG.1

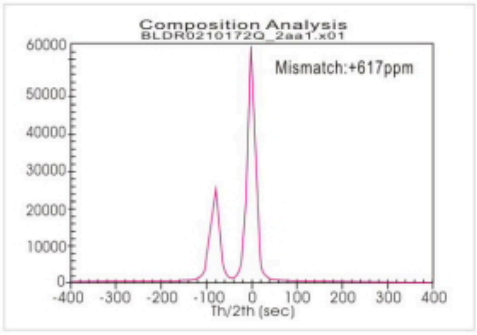

FIG.2

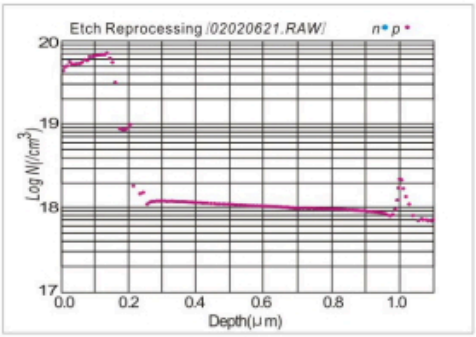

FIG.3

Device Performance

Characteristics	Symbol	Conditions	Typ.
Threshold Current	I_{th}		~20 mA
Operating Current	I_{OP}	@ 5 mW	~32 mA
Wavelength	λ		650~655 nm
Slope efficiency	η	@ 5 mW	~0.4 W/A
* Device structure: 4 μm x 250 μm Ridge Laser; as cleaved, @ R.T.			